

Low Phase Noise PECL VCXO (65MHz to 130MHz)

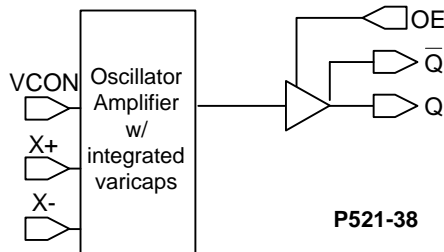
FEATURES

- 65MHz to 130MHz Fundamental Mode Crystal.
- Output range: 65MHz – 130MHz.
- Complementary PECL outputs.
- Selectable OE Logic (enable high or enable low).
- Integrated variable capacitors.
- High pull linearity: < 5%.
- +/- 125 ppm pull range
- Supports 2.5V or 3.3V-Power Supply.
- Available in die form.
- Thickness 10 mil.

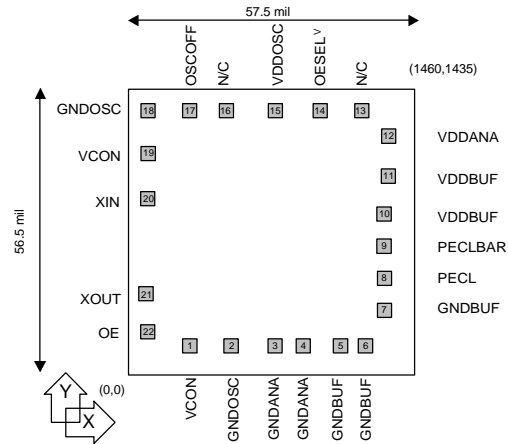
DESCRIPTIONS

P521-38 is a VCXO IC specifically designed to pull high frequency fundamental crystals. Its internal varicaps allow an on chip frequency pulling, controlled by the VCON input. The chip provides a low phase noise, low jitter PECL differential clock output.

BLOCK DIAGRAM



DIE CONFIGURATION



DIE SPECIFICATIONS

Name	Value
Size	56.5 x 57.5 mil
Reverse side	GND
Pad dimensions	80 micron x 80 micron
Thickness	10 mil

OUTPUT ENABLE LOGIC SELECTION

OESEL (Pad #14)	OECTRL (Pad #22)	State
0 (Default)	0 (Default)	Output enabled
	1	Tri-state
1	0	Tri-state
	1 (Default)	Output enabled

Pad #14, 22: Bond to GND to set to "0", bond to VDD to set to "1"
No connection results to "default" setting through internal pull-up/down.
Pad #22: Logical states defined by PECL V_{IH} and V_{IL} levels.

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PAD ASSIGNMENT AND DESCRIPTION

Pad #	Name	X (μm)	Y (μm)	Description
1	VCON	329.6	110.1	Control Voltage input. Use this pin to change the output frequency by varying the applied Control Voltage.
2	GNDOSC	498.3	110.0	GND connection for oscillator circuitry.
3	GNDANA	696.2	110.0	GND connection for analog circuitry.
4	GNDANA	825.0	110.0	GND connection for analog circuitry.
5	GNDBUF	973.6	110.0	GND connection for output buffer circuitry.
6	GNDBUF	1150.0	109.1	GND connection for output buffer circuitry.
7	GNDBUF (optional)	1183.6	302.2	GND connection for output buffer circuitry.
8	PECL	1183.6	452.3	PECL output
9	PECLBAR	1183.6	613.5	PECL complementary output.
10	VDDBUF (optional)	1182.4	745.9	VDD connection for output buffer circuitry. VDDBUF should be separately decoupled from other VDDs whenever possible.
11	VDDBUF	1252.4	903.6	VDD connection for output buffer circuitry. VDDBUF should be separately decoupled from other VDDs whenever possible.
12	VDDANA	1252.4	1081.3	VDD connection for analog circuitry. VDDANA should be separately decoupled from other VDDs whenever possible.
13	Not used	1058.5	1221.6	
14	OESEL	864.5	1221.6	Selector input to choose the OE control logic. See table on page 1.
15	VDDOSC	624.0	1222.7	VDD connection for oscillator circuitry. VDDOSC should be separately decoupled from other VDDs whenever possible.
16	Not used	467.1	1222.6	
17	OSCOFF	271.1	1222.6	Oscillator Off Selection input pad. When low, turns off the oscillator when output is disabled. When high (default), oscillator running when output is disabled. Internal pull-up
18	GNDOSC (optional)	109.4	1222.9	GND connection for oscillator circuitry.
19	VCON	108.9	1062.1	Control Voltage input. Use this pin to change the output frequency by varying the applied Control Voltage (internally connected to pad 1).
20	XIN	109.0	865.8	Crystal oscillator input pad.
21	XOUT	108.6	358.4	Crystal oscillator output pad.
22	OECTRL	108.6	146.5	OE input pad. See table on page 1.

Note: for optimal Phase Noise performance, it is recommended to bond all optional VDD and GND pads.

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ELECTRICAL SPECIFICATIONS

1. Absolute Maximum Ratings

PARAMETERS	SYMBOL	MIN.	MAX.	UNITS
Supply Voltage	V_{DD}		7	V
Input Voltage, dc	V_I	$V_{SS}-0.5$	$V_{DD}+0.5$	V
Output Voltage, dc	V_O	$V_{SS}-0.5$	$V_{DD}+0.5$	V
Storage Temperature	T_S	-65	150	°C
Ambient Operating Temperature	T_A	0	70	°C
Junction Temperature	T_J		125	°C
Lead Temperature (soldering, 10s)			260	°C
Input Static Discharge Voltage Protection			2	kV

Exposure of the device under conditions beyond the limits specified by Maximum Ratings for extended periods may cause permanent damage to the device and affect product reliability. These conditions represent a stress rating only, and functional operations of the device at these or any other conditions above the operational limits noted in this specification is not implied.

2. Crystal Specifications

PARAMETERS	SYMBOL	CONDITIONS	MIN.	TYP.	MAX.	UNITS
Crystal Resonator Frequency	F_{XIN}	Parallel Fundamental Mode	65		130	MHz
Crystal Loading Rating	$C_L (xtal)$	Die at VCON = 1.65V		7.5		pF
Interelectrode Capacitance	C_0				3.5	pF
Crystal Pullability	$C_0/C_1 (xtal)$	AT cut			250	-
Recommended ESR	R_E	AT cut			30	Ω

3. Voltage Control Crystal Oscillator

PARAMETERS	SYMBOL	CONDITIONS	MIN.	TYP.	MAX.	UNITS
VCXO Stabilization Time *	$T_{VCXOSTB}$	From power valid		10		ms
VCXO Tuning Range		XTAL $C_0/C_1 < 250$	250*			ppm
CLK output pullability		$0V \leq VCON \leq 3.3V$ at room temperature		$\pm 80^*$		ppm
On-chip Varicaps control range		$VCON = 0$ to 3.3V		4 – 18*		pF
Linearity				4*	5*	%
VCXO Tuning Characteristic				65		ppm/V
VCON input impedance			2000			k Ω
VCON modulation BW		$0V \leq VCON \leq 3.3V, -3dB$	25			kHz

Note: Parameters denoted with an asterisk (*) represent nominal characterization data and are not production tested to any specific limits.

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4. General Electrical Specifications

PARAMETERS	SYMBOL	CONDITIONS	MIN.	TYP.	MAX.	UNITS
Supply Current (Loaded Outputs)	I _{DD}	at 3.3V @ 77.76MHz			45	mA
Output valid after OE enabled		Oscillator off		10		ms
		Oscillator on			1	
Operating Voltage	V _{DD}		2.25		3.63	V
Output Clock Duty Cycle		@ V _{dd} - 1.3V (PECL)	45	50	55	%
Short Circuit Current				±50		mA

5. Jitter specifications

PARAMETERS	CONDITIONS	MIN.	TYP.	MAX.	UNITS
Period jitter RMS at 77.76MHz	At 77.76MHz, with capacitive decoupling between VDD and GND. Over 10,000 cycles		2.5		ps
Period jitter peak-to-peak at 77.76MHz			18.5	20	
Accumulated jitter RMS at 77.76MHz	At 77.76MHz, with capacitive decoupling between VDD and GND. Over 1,000,000 cycles.		2.5		ps
Accumulated jitter peak-to-peak at 77.76MHz			24	27	
Random Jitter	"RJ" measured on Wavecrest SIA 3000		2.5		ps
Integrated jitter RMS at 77.76MHz	Integrated 12 kHz to 20 MHz		0.5	0.7	ps

Measured on Wavecrest SIA 3000

6. Phase noise specifications

PARAMETERS	FREQUENCY	10Hz	100Hz	1kHz	10kHz	100kHz	1MHz	UNITS
Phase Noise relative to carrier	77.76MHz	-75	-100	-125	-140	-145	-150	dBc/Hz

Note: Phase Noise measured at VCON = 0V

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7. PECL Electrical Characteristics

PARAMETERS	SYMBOL	CONDITIONS	MIN.	MAX.	UNITS
Output High Voltage	V_{OH}	$R_L = 50 \Omega$ to $(V_{DD} - 2V)$ (see figure)	$V_{DD} - 1.025$		V
Output Low Voltage	V_{OL}			$V_{DD} - 1.620$	V

8. PECL Switching Characteristics

PARAMETERS	SYMBOL	CONDITIONS	MIN.	TYP.	MAX.	UNITS
Clock Rise Time	t_r	@20/80% - PECL		0.6	1.5	ns
Clock Fall Time	t_f	@80/20% - PECL		0.5	1.5	ns

